



#### DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

- Dual N-Channel MOSFET
- Low On-Resistance (1.0V max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected up to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

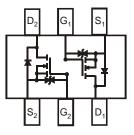
#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.006 grams (approximate)





Top View



Top View Internal Schematic

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN5L06DWK-7	SOT363	3000/Tape & Reel

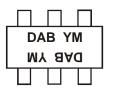
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



DAB = Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Notes:

Month	Jan	Feb	Mar	Apr	Mav	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	Т	U	V		Z	А	В	С	D	E	F	G
Year	2006	2007	2008		2012	2013	2014	2015	2016	2017	2018	2019



### Maximum Ratings @T<sub>A</sub> = +25°C unless otherwise specified

Chara	acteristic	Symbol	Value	Unit
Drain Source Voltage		V <sub>DSS</sub>	50	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Drain Current	Continuous	1-	305	m (
	Pulsed (Note 6)	ID	800	mA

## Thermal Characteristics @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	250	mW
Thermal Resistance, Junction to Ambient	R <sub>θ</sub> JA	500	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-65 to +150	С°

#### Electrical Characteristics @T<sub>A</sub> = +25°C unless otherwise specified

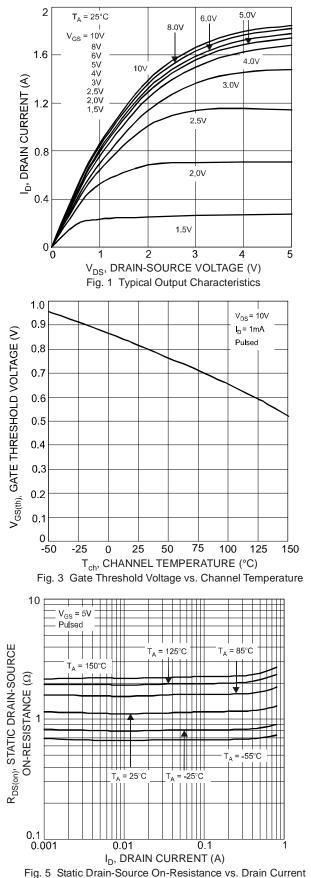
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•		
Drain-Source Breakdown Voltage	<b>BV</b> <sub>DSS</sub>	50	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current @ T <sub>C</sub> =	+25°C I <sub>DSS</sub>		_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
				1	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Body Leakage	I <sub>GSS</sub>	_	—	500	'nΑ	$V_{GS} = \pm 10V, V_{DS} = 0V$
				50	nA	$V_{GS} = \pm 5V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.49	—	1.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
			_	3.0		$V_{GS} = 1.8V, I_D = 50mA$
Static Drain-Source On-Resistance	RDS (ON)	_	—	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
			—	2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.4	_	А	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	Y <sub>fs</sub>	200	_	_	mS	V <sub>DS</sub> =10V, I <sub>D</sub> = 0.2A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>			50	pF	
Output Capacitance	C <sub>oss</sub>		_	25	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	5.0	pF	

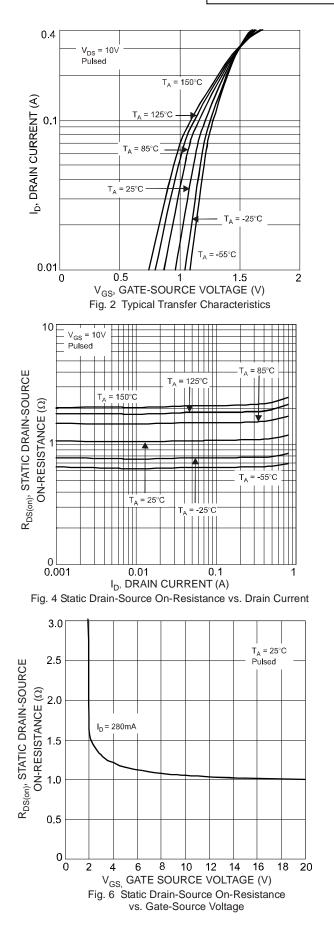
Notes: 5. Device mounted on FR-4 PCB.

Pulse width ≤10μS, Duty Cycle ≤1%.
Short duration pulse test used to minimize self-heating effect.

# DMN5L06DWK

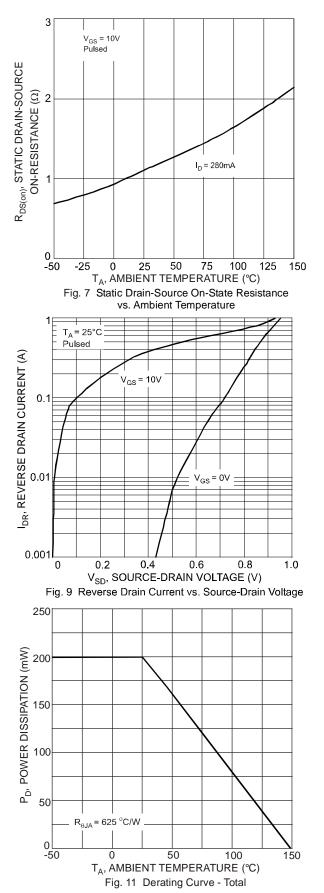


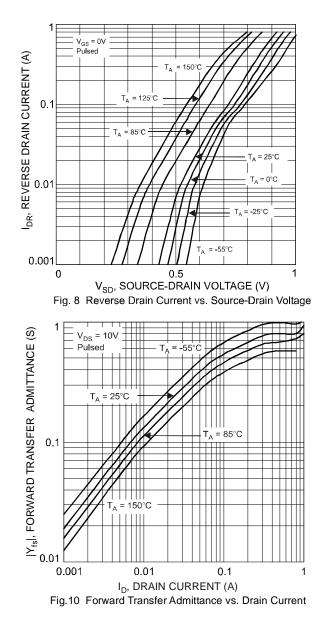




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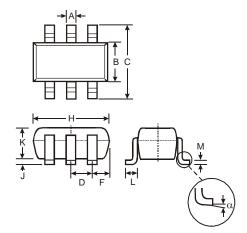






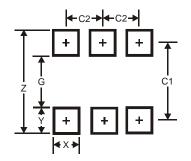


# Package Outline Dimensions



SOT363						
Dim	Min	Max	Тур			
Α	0.10	0.30	0.25			
В	1.15	1.35	1.30			
С	2.00	2.20	2.10			
D	0.65 Typ					
F	0.40	0.45	0.425			
Н	1.80	2.20	2.15			
J	0	0.10	0.05			
Κ	0.90	1.00	1.00			
L	0.25	0.40	0.30			
М	0.10	0.22	0.11			
α	0°	8°	-			
All	Dimen	isions i	n mm			

# Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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